SILICON NPN TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

2SC3230

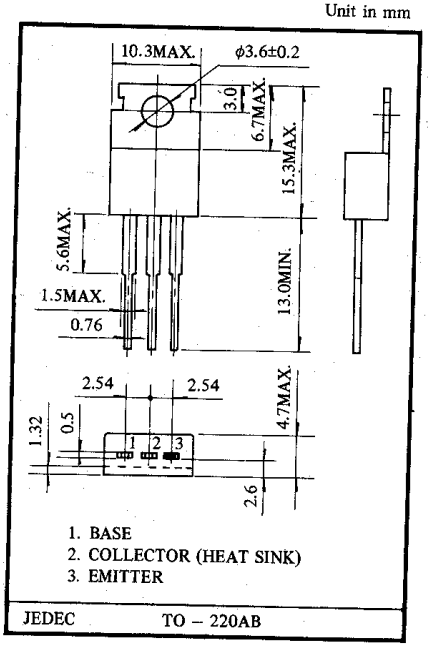
APPLICATIONS

- Power Amplifier Applications
- Car Radio, Car Stereo Output Stage Amplifier Applications.

FEATURES

- Complementary to 2SA 1276
  5 Watts Output Applications.

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC TO – 220AB

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3	A

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	−3	A
Collector Power Dissipation(Tc=25℃)	P_C	10	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	Tstg	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=20V, I_E=0	—	—	1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA, I_B=0	30	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5	—	—	V
DC Current Gain	h_{FE}(1)(Note)	V_{CE}=2V, I_C=0.5A	70	—	240	
	h_{FE}(2)	V_{CE}=2V, I_C=2.5A	25	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2A, I_B=0.2A	—	0.3	0.8	V
Base-Emitter Voltage	V_{BE}	V_{CE}=2V, I_C=0.5A	—	0.75	1.0	V
Transition Frequency	f_T	V_{CE}=2V, I_C=0.5A	—	100	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	—	35	—	pF

NOTE: According to hFE(1)' Classified as follows.

O	70 – 140	Y	120 – 240

KEC